## MAINTENANCE MANUAL

LBI30422 (DF3165) (DF3171) IMTS

# 138-174 MHz EXCITER BOARDS 19D416859GI-G4 AND 19D430230GI-G4

TABLE OF CONTENTS	
	Page
DESCRIPTION	1
CIRCUIT ANALYSIS	
OUTLINE DIAGRAM	· e
SCHEMATIC DIAGRAMS	7 & 9
PARTS LIST AND PRODUCTION CHANGES	8 & 10
ILLUSTRATIONS	
Figure 1 - Typical Crystal Characteristics	2
Figure 2 - Equivalent ICOM Circuit	3
Figure 3 - Simplified Audio IC	3

### DESCRIPTION

This exciter for MASTR® II uses nine transistors and one integrated circuit to drive the PA assembly. The exciter can be equipped with up to eight Integrated Circuit Oscillator Modules (ICOMs). The ICOM crystal frequency ranges from approximately 11.5 to 14.5 megahertz, and the crystal frequency is multiplied 12 times.

Audio, supply voltages and control functions are connected from the system board to the exciter board through P902.

Centralized metering jack J103 is provided for use with GE Test Set Model 4EX3A11 or Test Kit 4EX8K12. The test set meters the modulator, multiplier, and amplifier stages, and the regulated 10 Volts.

## CIRCUIT ANALYSIS

ICOMS

Three different types of ICOMs are available for use in the exciter. Each of the ICOMs contains a crystal-controlled Colpitts oscillator, and two of the ICOMs contain compensator ICs. The different ICOMs are:

- 5C-ICOM contains an oscillator and a 5 part-per-million (±0.0005%) compensator IC. Provides compensation for EC-ICOMs.
- EC-ICOM contains an oscillator only. Requires external compensation from a 5C-ICOM.
- 2C-ICOM contains an oscillator and a 2 PPM (±0.0002%) compensator IC. Will not provide compensation for an EC-ICOM.

The ICOMs are enclosed in an RF shielded can with the type ICOM (5C-ICOM, EC-ICOM or 2C-ICOM) printed on the top of the can. Access to the oscillator trimmer

is obtained through a hole on the top of the can.

For proper operation, be sure ICOM case makes contact with fingers on the the RF shield on the exciter board. Also, the pins on the exciter bottom cover must make contact with the RF shield.

Frequency selection is accomplished by switching the ICOM keying lead (terminal 6) to A- by means of the frequency selector switch on the control unit. In single-frequency radios, a jumper from H9 to H10 in the control unit connects terminal 6 of the ICOM to A-. The oscillator is turned on by applying a keyed +10 Volts to the external oscillator load resistor.

All ICOMs are individually compensated at the factory and cannot be repaired in the field. Any attempt to repair or change an ICOM frequency will void the warranty.

In Standard 5 PPM radios using EC-ICOMs, at least one 5C-ICOM must be used. The 5C-ICOM is normally used in the receiver Fl position, but can be used in any transmit or receive position. One 5C-ICOM can provide compensation for up to 15 EC-ICOMs in the transmit and receiver. Should the 5C-ICOM compensator fail in the open mode, the EC-ICOMs will still maintain 2 PPM frequency stability from 0°C to 55°C (+32°F to 131°F) due to the regulated compensation voltage (5 Volts) from the 10 Volt regulator IC. If desired, up to 16 5C-ICOMs may be used in the radio.

The 2C-ICOMs are self-compensated at 2 PPM and will not provide compensation for EC-ICOMs.

### Oscillator Circuit

The quartz crystals used in ICOMs exhibit the traditional "S" curve characteristics



of output frequency versus operating temperature.

At both the coldest and hottest temperatures, the frequency increases with increasing temperature, in the middle temperature range (approximately  $0\,^{\circ}\text{C}$  to  $+55\,^{\circ}\text{C}$ ), frequency decreases with increasing temperature.

Since the rate of change is nearly linear over the mid-temperature range, the output frequency change can be compensated by choosing a parallel compensation capacitor with a temperature coefficient approximately equal and opposite that of the crystal.

Figure 1 shows the typical performance of an uncompensated crystal as well as the typical performance of a crystal which has been matched with a properly chosen compensation capacitor.

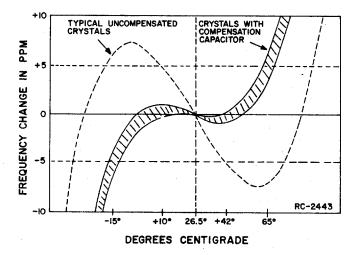


Figure 1 - Typical Crystal Characteristics

At temperatures above and below the mid-range, additional compensation must be introduced. An externally generated compensation voltage is applied to a varactor (voltage-variable capacitor) which is in parallel with the crystal.

A constant bias of 5 Volts (provided from Regulator IC U901 in parallel with the compensator) established the varactor capacity at a constant value over the entire mid-temperature range. With no additional compensation, all of the oscillators will provide 2 PPM frequency stability from 0°C to 55°C (+32°F to 131°F).

#### Compensator Circuits

Both the 5C-ICOMs and 2C-ICOMs are temperature compensated at both ends of the temperature range to provide instant frequency compensation. An equivalent ICOM circuit is shown in Figure 2.

The cold end compensation circuit does not operate at temperatures above  $0\,^{\circ}\text{C}$ . When the temperature drops below  $0\,^{\circ}\text{C}$ , the circuit is activated. As the temperature decreases, the equivalent resistance de-

creases and the compensation voltage increases.

An increase in compensation voltage decreases the capacitance of the varactor in the oscillator, thereby increasing the output frequency of the ICOM.

The hot end compensation circuit does not operate at temperatures below  $+55\,^{\circ}\text{C}$ . When the temperature rises above  $+55\,^{\circ}\text{C}$ , the circuit is activated. As the temperature increases, the equivalent resistance decreases and the compensation voltage decreases. The decrease in compensation voltage increases the capacity of the varactor, decreasing the output frequency of the ICOM.

SERVICE NOTE: Proper ICOM operation is dependent on the closely-controlled input voltages from the 10 Volt regulator. Should all of the ICOMs shift off frequency, check the 10 Volt regulator module.

#### AUDIO IC

The transmitter audio circuitry is contained in audio IC UlO1. A simplified drawing of the audio IC is shown in Figure 3.

Audio from the microphone at pin 12 is coupled through pre-emphasis capacitor C1 to the base of Q1 in the operational amplifier-limiter circuit. Collector voltage for the transistorized microphone pre-amplifier is supplied from pin 11 through microphone collector load resistor R18 to pin 12.

The operational amplifier-limiter circuit consists of Q1, Q2, and Q3. Q3 provides limiting at high signal levels. The gain of the operational amplifier circuit is fixed by negative feedback through R19, R20 and the resistance in the network (Pin 9).

The output of Q3 is coupled through a de-emphasis network (R10 and C3) to an active post-limiter filter consisting of C4, C5, C6, R11, R12, R13, R15, R17 and Q4.

Following the post-limiter filter is class A amplifier Q5. The output of Q5 is coupled through MOD ADJUST potentiometer R104 and resistors R108 and R125 to the phase modulators.

SERVICE NOTE: If the DC voltages to the Audio IC are correct and no audio output can be obtained, replace Ul01.

For radios equipped with Channel Guard, tone from the encoder is applied to the phase modulators through CHANNEL GUARD MOD ADJUST potentiometer R105, and resistors R112, R105 and R127. Instructions for setting R105 are contained in the modulation adjustment section of the Transmitter Alignment Procedure.

# BUFFER, PHASE MODULATORS & AMPLIFIERS

The output at pin 3 of the selected ICOM is coupled through buffer-amplifier Q101 to the first modulator stage. The first phase modulator is varactor (voltage-variable capacitor) CV101 in series with tunable coil T101. This network appears as a series-resonant circuit to the RF output of the

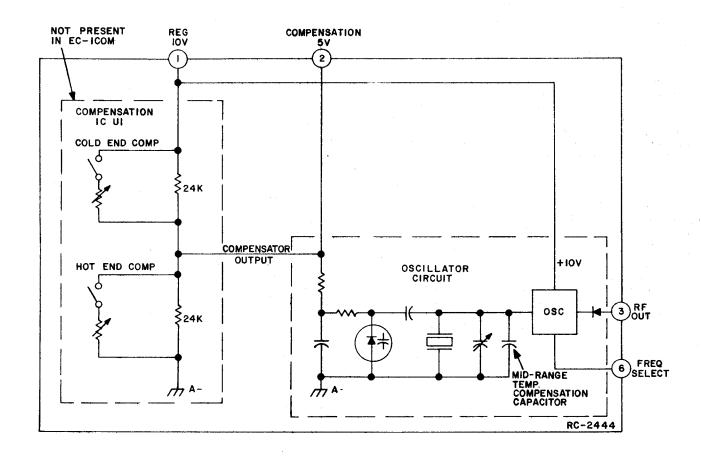


Figure 2 - Equivalent ICOM Circuit

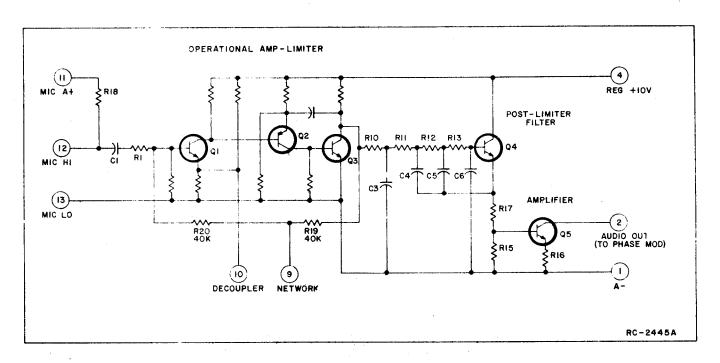


Figure 3 - Simplified Audio IC

oscillator. An audio signal applied to the modulator circuit through blocking capacitor Cl07 varies the bias of CV101, resulting in a phase modulated output. A voltage divider network (R110 and R111) provides the proper bias for varactors CV101, CV102 and CV103.

The output of the first modulator is coupled through blocking capacitor Cll3 to the base of Class A amplifier Ql02. The first modulator stage is metered through a metering network consisting of Cll5, Rl18, and CR101. Diodes CR102 and CR103 remove any amplitude modulation in the modulator output.

Following Q102 is another Class A amplifier, Q103. The output of Q103 is applied to the second modulator stage. The second modulator consists of two cascaded modulator circuits consisting of CV102, T102, T103 and CV103. Following the second modulator is a Class A amplifier, Q104. The output of the second modulator stage is metered through C123, R132, and CR104 and is applied to the base of buffer Q105. Diodes CR105 and CR106 remove any amplitude modulation in the second modulator output.

BUFFER, MULTIPLIERS & AMPLIFIER

Buffer Q105 is saturated when no RF signal is present. Applying an RF signal to Q105 provides a sawtooth waveform at its collector to drive the class C tripler, Q106. The tripler stage is metered through R138. The output of Q106 is coupled through tuned circuits T104 and T105 to the base of doubler Q107. T104 & T105 are tuned to one-fourth of the operating frequency. The doubler stage is metered through R141.

The output of Q107 is coupled through tuned circuits T106 & T107 to the base of second doubler Q108. T106 & T107 are tuned to one-half the operating frequency. Q108 is metered through R146.

The output of Q108 is coupled through three tuned circuits (T108, T109, and T110) to the base of amplifier Q109. The circuits are tuned to the transmitter operating frequency.

Q109 is a class C amplifier, and is metered through R148. The amplifier collector circuit consists of T111, C154, C155, T112, and C157, and matches the amplifier output to the input of the power amplifier assembly.

GENERAL ELECTRIC COMPANY• MOBILE COMMUNICATIONS DIVISION WORLD HEADQUARTERS•LYNCHBURG, VIRGINIA 24502 U.S.A.



T104

SOLDER SIDE

( C 2 3 )

TI07

Y 102 Y 102 RIO3(\*) | 13\*

Issue 6

(19D424489, Rev. 2)

Y107 XY107 XY107 XY103 XY105 XY1

(oClO24 foClO14 . RIOI .

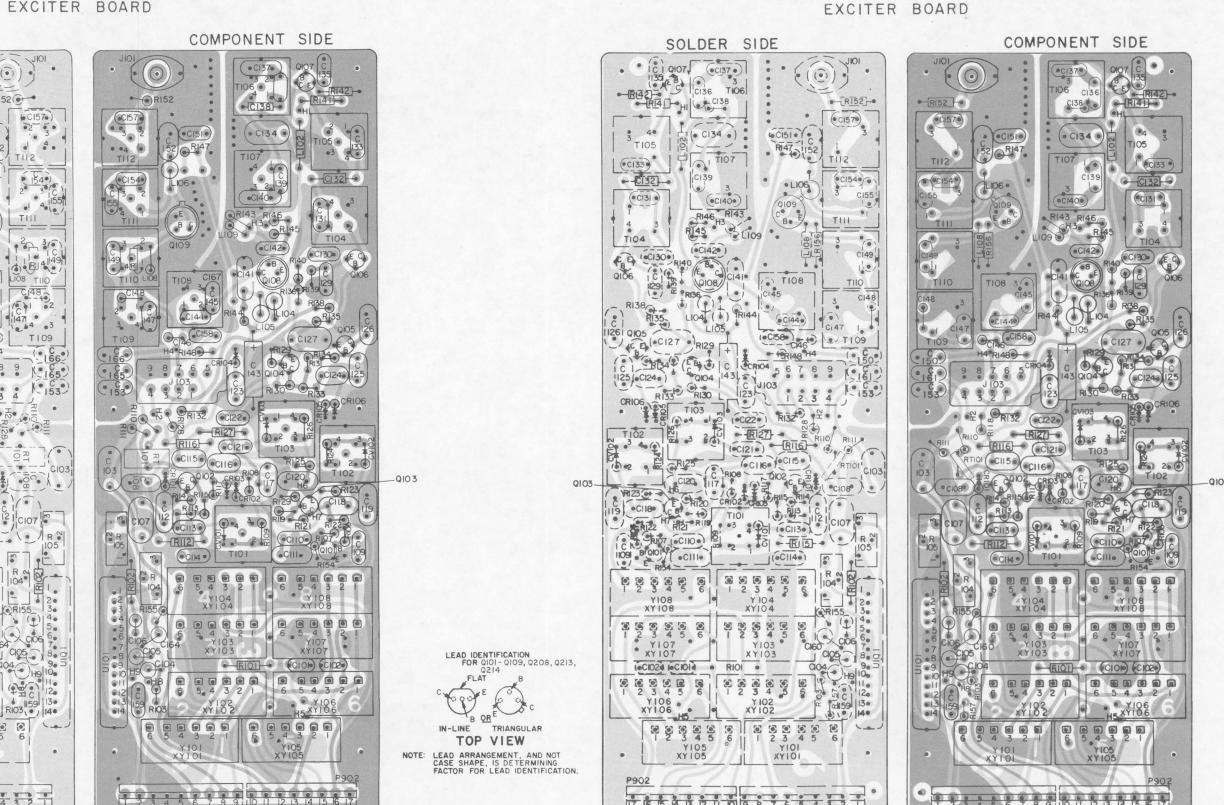
R152(0)

02 0

· 3/6)

(19D430229, Sh. 2, Rev. 9) (19D430229, Sh. 3, Rev. 8)

(19D430343, Rev. 5)

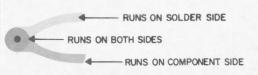


# OUTLINE DIAGRAM

6

138—174 MHz. EXCITER BOARD 19D416859G1-G4

(19D423545, Sh. 2, Rev. 4)

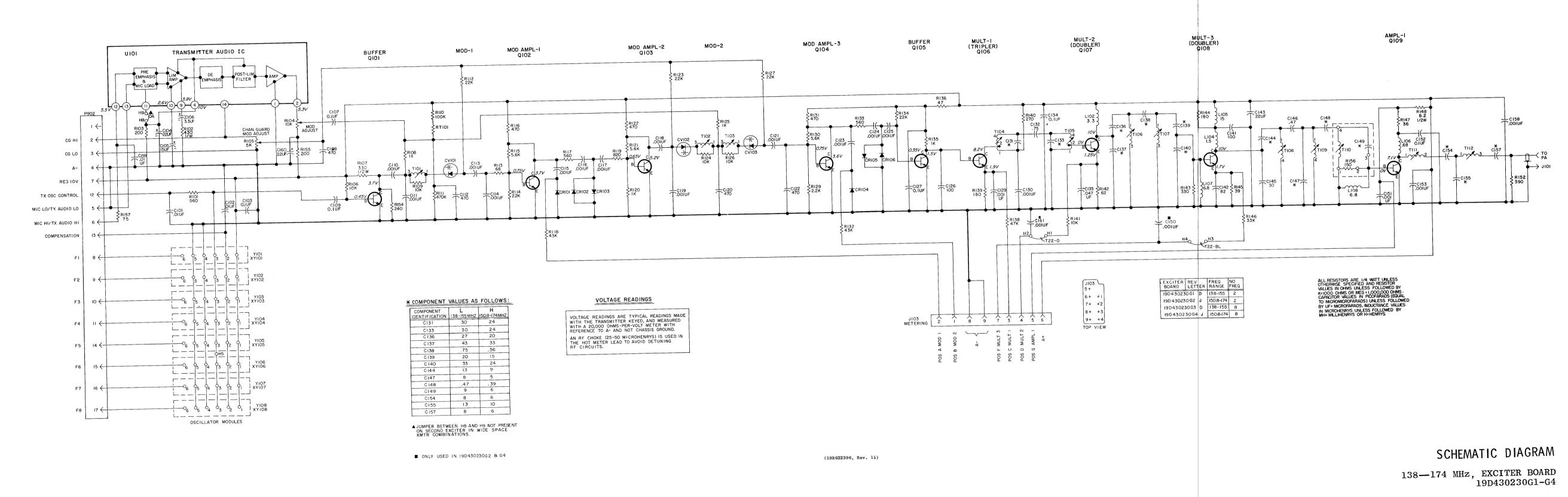


(19D423545, Sh. 2, Rev. 4) (19D423545, Sh. 3, Rev. 3)

# OUTLINE DIAGRAM

138—174 MHz, EXCITER BOARD 19D430230G1-G4

(19D430229, Sh. 2, Rev. 9)



Issue 3

# LBI30422

# PARTS LIST

	138	-174 MHz EXCTER BOARD 19D430230G1-G4 ISSUE 3	C137L C137H
			C138L
			C138H
			C139L
SYMBOL	GE PART NO.	DESCRIPTION	С139Н
		19D430230G1 2 FREQ 138-155 MHz (L)	02002
		19D43023061 2 FREQ 150.8-174 MHz(H) 19D43023063 8 FREQ 138-155 MHz (L) 19D43023064 8 FREQ 150.8-174 MHz(H)	C140L
			C140H
C101 and	19A116080P1	Polyester: 0.01 µf ±20%, 50 VDCW.	C141 C142
C102 C103	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.	C143
C104	5496267P10	Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague	CLAS
C105	5496267P14	Type 150D.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague	C144L
C106	5496267 <b>P</b> 9	Type 150D.  Tantalum: 3.3 µf ±20%, 15 VDCW; sim to Sprague	C144H
		Type 150D.	C145
C107	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.  Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to	C146
C108	5494481P107	RMC Type JF Discap.	C147L
CT08	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.	С147Н
C110	5494481P111	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	1
C111	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C148L C148H
C112	5494481P107	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	C149L
Cll3 thru Cll7	5494481P111	RMC Type JF Discap.	C150
C118 and C119	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C151
C119	7489162P43	Silver mica: 470 pf ±5%, 300 VDCW; sim to Electro Motive Type DM-15.	C152 C153
C121	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C154L
C122	5494481P107	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C154H
C123 thru	5494481P111	Ceramic disc: 1000 pf $\pm 20\%$ , 1000 VDCW; sim to RMC Type JF Discap.	C155L
C125 C126	19A700105P34	Mica: 100 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	С155Н
C127	19A116080P107	Polyester: 10 µr ±10%, 50 VDCW.	C157L
C129 and	5494481P111	Ceramic disc: 1000 pf $\pm 20\%$ , 1000 VDCW; sim to RMC Type JF Discap.	C157H
C130;	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.	C158
C131H	5496219P248	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef -80 PPM.	C159
C132	5491601P118	Phenolic: 0.75 pf ±5%, 500 VDCW.	C160
C133L	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef	C161
C133H	5496219P248	-80 PPM.  Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef -80 PPM.	
	1041160000307	-80 PPM. Polyester: 0.1 µf ±10%, 50 VDCW.	
C134	19A116080P107	Polyester: 0.047 µf ±10%, 50 VDCW.	CR10
C135	19A116080P105	Ceramic disc: 27 pf ±5%, 500 VDCW, temp coef	CR10
C136L		-80 PPM.	thru

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
STMDOL	de l'illi				JACKS AND RECEPTACLES	R124	19A700106P87	Composition: 10K ohms ±5%, 1/4 w.
C137L	5496219P254	Ceramic disc: 43 pf ±5%, 500 VDCW, temp coef -80 PPM.	J101	19A130924G1	Receptacle, coaxial: sim to Cinch 14H11613.	R125	19A700106P63	Composition: 1K ohms ±5%, 1/4 w.
C137H	5496219P251	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef	J103	19B219374G1	Connector. Includes:	R126	19A700106P87	Composition: 10K ohms ±5%, 1/4 w.
		-80 PPM.	•	19A116651P1	Contacts. (9).	R127	19A700106P95	Composition; 22K ohms ±5%, 1/4 w.
C138L	5491601P118	Phenolic: 0.75 pf ±5%, 500 VDCW.  Phenolic: 0.56 pf ±5%, 500 VDCW.			INDUCTORS	R129	19A700106P71	Composition: 2.2K ohms ±5%, 1/4 w.
C138H	19A700013P10 5496219P246	Ceramic disc: 20 pf ±5%, 500 VDCW, temp coef		19A700024P19	Coil, RF: 3.3 µh ±10%, 0.85 ohms DC res max.	R130	19A700106P81	Composition: 5.6K ohms ±5%, 1/4 w.
C139L	54962197246	-80 PPM.	L102*	19A700024P19	In G1 & G3 of REV C & earlier;	R131	19A700106P55	Composition: 470 ohms ±5%, 1/4 w.
С139Н	5496219P244	Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef -80 PPM.			In G2 & G4 of REV H & earlier:	R132	3R152P433J	Composition: 43K ohms ±5%, 1/4 w.
C140L	5496219 <b>P</b> 251	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef		19B209420P130	Coil, RF: 27.0 µh ±10%, 3.60 ohms DC res max; sim to Jeffers 441316-5K.	R133	19A700106P57	Composition: 560 ohms ±5%, 1/4 w.  Composition: 22K ohms ±5%, 1/4 w.
		-80 PPM.	L104	19A700000P14	Coil, RF: 1.5 $\mu$ h $\pm 10\%$ , 0.485 ohms DC res max.	R134	19A700106P95 19A700106P63	Composition: 1K ohms ±5%, 1/4 w.
C140H	5496219P248	Ceramic disc: 24 pf ±5%, 500 VDCw, temp coef -80 PPM.	L105	19A700000P25	Coil, RF: 15.0 µh ±10%, 1.20 ohms DC res max.	R135	19A700106P31	Composition: 47 ohms ±5%, 1/4 w.
C141	5490008P127	Silver mica: 100 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.	L106	19A700000P10	Coil, RF: 0.68 µh ±10%, 0.15 ohms DC res max.	R138	19A700106P103	Composition: 47K ohms ±5%, 1/4 w.
	10.500105000	Mica: 82 pf ±5%, 500 VDCw; sim to Electro	L107	19A700024P23	Coil, RF: 6.8 µh ±10%, 2.00 ohms DC res max.	R139	19A700106P45	Comosition: 180 ohms ±5%, 1/4 w.
C142	19A700105P32	Motive Type DM-15.	and L108			R140	19A700106P49	Composition: 270 ohms ±5%, 1/4 w.
C143	5496267P10	Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D.				R141	19A700106P87	Composition: 10K ohms ±5%, 1/4 w.
C144L	5496219P243	Ceramic disc: 13 pf ±15%, 500 VDCW, temp coef	P902		Includes:	R142	3R152P620J	Composition: 62 ohms ±5%, 1/4 w.
CITAL		-80 PPM.		19B219594P2	Contact strip: 8 pins.	R143	19A700106P51	Composition: 330 ohms ±5%, 1/4 w.
C144H	5496219P240	Ceramic disc: 9.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.		19B219594P3	Contact strip: 9 pins.	R144	19A700106P45	Composition: 180 ohms $\pm 5\%$ , $1/4$ w.
C145	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef			TRANSISTORS	R145	19A700106P29	Composition: 39 ohms ±5%, 1/4 w.
	Į.	-80 PPM.	Q101	19A115330P1	Silicon, NPN.	R146	3R152P333K	Composition: 33K ohms ±10%, 1/4 w.
C146	19A700013P9	Phenolic: 0.47 pf ±5%, 500 YDCW.  Ceramic disc: 8.0 pf ±0.25 pf, 500 YDCW, temp	thru Q106			R147	3R152P360J	Composition: 36 ohms ±5%, 1/4 w.
C147L	549 62 19 P2 39	coef -80 PPM.	Q107	19A115328P1	Silicon, NPN.	R148	19A700113P13	Composition: 8.2 ohms ±5%, 1/2 w.
C147H	5496219P236	Ceramic disc: 5.0 pf ±0.25 pf, 500 VDCW, temp	Q108*	19A116868P1	Silicon, NPN; sim to Type 2N4427.	R152	19A700106P53	Composition: 390 ohms ±5%, 1/4 w.
1 4 0 -	19A700013P9	Phenolic: 0.47 pf ±5%, 500 VDCW.			In G1 & G3 of REV B & earlier: In G2 & G4 of REV G & earlier:	R154	3R152P241J	Composition: 240 ohms ±5%, 1/4 w.
C148L C148H	19A700013P8	Phenolic: 0.39 pf ±5%, 500 VDCW.	1	19A115329P1	Silicon, NPN.		ŀ	
CIAN	15			10.11.10				
							10.1700106P4C	Composition: 200 ohms ±5%, 1/4 w.
		Ceramic disc: 9.0 ±0.25 pf, 500 VDCW, temp coef	1		WWW 2W4497	R155	19A700106P46 19A700106P43	Composition: 150 ohms ±5%, 1/4 w.
C149L	5496219P240	-80 PPM.	Q109	19A116868P1	Silicon, NPN; sim to Type 2N4427.	R156	19A700106P36	Garnagition: 75 ohms +5%, 1/4 w. Added to
C149H	5496219P237	Ceramic disc: 6.0 pf ±0.25 pf, 500 VDCW, temp			RESISTORS	R157*	198700100130	G1 & G3 by REV A, G2, G4 by REV B.
		Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	R101	19A700106P57	Composition: 560 ohms ±5%, 1/4 w.			THERMISTORS
C150	5494481P111	RMC Type JF Discap.	R102	3R152P431J	Composition: 430 ohms ±5%, 1/4 w.	RT101*	5490828 <b>P</b> 23	Thermistor: 3600 ohms ±10%, color code black; si to Carborundum Type 783F-1. Added to G1 & G3 by
C151	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	R103	19A700106P46	Composition: 200 ohms ±5%, 1/4 w.			REV B. Added to G2 & G4 by REV C.
C152	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.	R104	19B209358P106	Variable, carbon film: approx 300 to 10K ohms ±10%, 0.25 w; sim to CTS Type X-201.			TRANS FOR MERS
C152	19A116655P19	Ceremic disc: 1000 pf ±20%, 1000 VDCW; sim to	R105	19B209358P105	to the film: approx 200 to 5K ohms			wire size No. 34 AWG; sim to
C155	10.1.2000	RMC Type JF Discap.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp	RIOS		±10%, 0.25 w; sim to CTS Type x-201.	T101L	19C307171P102	Paul Snith Co. Sample No. 111374 Od 2.
C154L	5496219P239	coef -80 PPM.	R106	19A700106P87	Composition: 10K ohms $\pm 5\%$ , $1/4$ w. Composition: 330 ohms $\pm 5\%$ , $1/2$ w.	TlOlH	19C307171P107	Coil, RF: variable, wire size No. 34 AWG; sim to Paul Smith Co. Sample No. 031579-JT-1.
C154H	5496219P237	Ceramic disc: 6.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.	R107	19A700113P51	Composition: 1K ohms ±5%, 1/4 w.	T102L	19C307171P102	wire size No. 34 AWG: sim to
İ		coef -80 PPM.  Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef	R108	19A700106P63	Composition: 10K ohms ±5%, 1/4 w.	TIOZE	10000, 1111 102	Paul Smith Co. Sample No. 1113/4-00-1.
C155L	5496219P243	-80 PPM.	R109	19A700106P87	Composition: 100K ohms ±5%, 1/4 w.	т102Н	19C307171P107	Coil, RF: variable, wire size No. 34 AWG; sim to Paul Smith Co. Sample No. 031579-JT-1.
C155H	5496219P241	Ceramic disc: 10 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.	R110	3R152P474J	Composition: 470K ohms ±5%, 1/4 w. Added to	T103L	19C307171P102	Coil, RF: variable, wire size No. 34 AwG; sim to Paul Smith Co. Sample No. 111374-OG-1.
a1571	5496219P239	Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp	R111*	3K152F4745	G2 & G4 by REV E.			tall wing size No. 34 AWG: sim to
C157L	54962151255	coef -80 PPM.	R112	19A700106P95	Composition: 22K ohms ±5%, 1/4 w.	Т103Н	19C307171P107	Paul Smith Co. Sample No. 0310.5 01
С157Н	5496219P237	Ceramic disc: 6.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.	R113	19A700106P35	Composition: 68 ohms ±5%, 1/4 w.	T104	19C307170P301	Coil, RF; variable, wire size No. 20 AWG; sim to Paul Smith Co. Sample No. 082874-WS-2.
C158	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	R114	19A700106P71	Composition: 2.2K ohms ±5%, 1/4 w.		1000071700202	with size No. 20 AWG; sim t
		RMC Type JF Discap.  Polyester: 0.01 µf ±20%, 50 VDCW.	R115	19A700106P81	Composition: 5.6K ohms $\pm 5\%$ , $1/4$ w.  Composition: 470 ohms $\pm 5\%$ , $1/4$ w.	T105	19C307170P302	Paul Smith Co. Sample No. 082811 115 01
C159	19A116080P1	Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague	R116	19A700106P55	Composition: 560 ohms ±5%, 1/4 w.	т106	19C307170P303	Coil, RF: variable, wire size No. 20 AWG; sim t Paul Smith Co. Sample No. 071774-OG-6.
C160	5496267P10	Type 150D.	R117	19A700106P57	Composition: 43K ohms ±5%, 1/4 w.	and T107		
C161	5494481P111	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	R118	3R152P433J	Composition: 820 ohms ±5%, 1/4 w.	T108	19C307169P201	Coil, RF: variable, wire size No. 20 AWG; sim t Paul Smith Co. Sample No. 091774-WS-1.
		i 1	R119	19A700106P61	Composition: 1K ohms ±5%, 1/4 w.	T110		wire size No. 20 AWG; sim t
		DIODES AND RECTIFIERS	R120	19A700106P63	Composition: 5.6K ohms ±5%, 1/4 w.	Tlll and	19C307170P304	Coil, RF: variable, wire size No. 20 ANG, Bland Paul Smith Co. Sample No. 071774-OG-3.
CR101	19A115250Pl	Silicon, fast recovery, 225 mA, 50 PIV.	R121	19A700106P51	Composition: 470 ohms ±5%, 1/4 w.	T112		
thru CR106		Silicon, capacitive: 33 pf ±20%, at 4 VDC.	R122 R123	19A700106P95	Composition: 22K ohms ±5%, 1/4 w.	11		

GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
19A700106P87 19A700106P63 19A700106P87 19A700106P95 19A700106P81 19A700106P55 3R152P433J 19A700106P57 19A700106P95	Composition: 10K ohms ±5%, 1/4 w. Composition: 1K ohms ±5%, 1/4 w. Composition: 10K ohms ±5%, 1/4 w. Composition: 22K ohms ±5%, 1/4 w. Composition: 2.2K ohms ±5%, 1/4 w. Composition: 470 ohms ±5%, 1/4 w. Composition: 43K ohms ±5%, 1/4 w. Composition: 560 ohms ±5%, 1/4 w. Composition: 22K ohms ±5%, 1/4 w. Composition: 1K ohms ±5%, 1/4 w.	W101  XY101 thru XY108	19D416542G2 19A701785P1	Audio Transmitter.
19A700106P31 19A700106P103 19A700106P45 19A700106P49 19A700106P87	Composition: 47 ohms ±5%, 1/4 w.  Composition: 47K ohms ±5%, 1/4 w.  Comosition: 180 ohms ±5%, 1/4 w.  Composition: 270 ohms ±5%, 1/4 w.  Composition: 10K ohms ±5%, 1/4 w.	Y101 thru Y108 Y101 thru Y108	19A129393G17	Externally compensated, ±5 PPM, 138-174 MHz.  Externally compensated, ±2 PPM, 138-174 MHz.
3R152P620J 19A700106P51 19A700106P45 19A700106P29 3R152P333K 3R152P360J 19A700113P13 19A700106P53 3R152P241J	Composition: 62 ohms ±5%, 1/4 w.  Composition: 330 ohms ±5%, 1/4 w.  Composition: 180 ohms ±5%, 1/4 w.  Composition: 39 ohms ±5%, 1/4 w.  Composition: 33K ohms ±10%, 1/4 w.  Composition: 36 ohms ±5%, 1/4 w.  Composition: 8.2 ohms ±5%, 1/2 w.  Composition: 390 ohms ±5%, 1/4 w.  Composition: 240 ohms ±5%, 1/4 w.		19A129424G2 4036555P1	MECHANICAL PARTS  Can. (Used with T101-T112).  Insulator, washer: nylon. (Used with Q108, Q109)

# PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A Exciter Board 19D430230G1, G3
  - To improve sensitivity. Added R157.
- REV. B To improve operation. Added RT101.
- REV. C To incorporate new transistor. Changed Q108.
- REV. D To improve carrier-to-noise ratio. Changed L102.
- REV. A Exciter Board 19D430230G2, G4 To improve transmitter stability. Added R152.
- REV. B Not incorporated.
- REV. C Not incorporated.
- REV. D To improve tuning at high end of split. Deleted R111.
- REV. E To improve tuning at high end of split. Added R111 and changed T101, T102 and T103.
- REV. F To improve sensitivity. Added R157.
- REV. G To improve operation. Added RT101.
- REV. H To incorporate new transistor. Changed Q108.
- REV. J To improve carrier-to-noise ratio. Changed L102.